

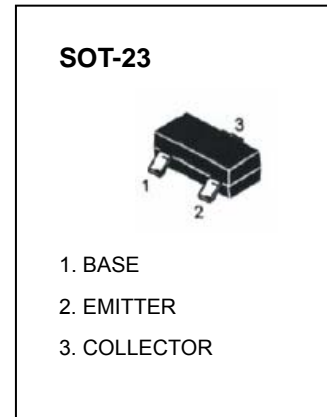
TRANSISTOR (NPN)

FEATURES

- Optimal for muting.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	30	V
V _{CE0}	Collector-Emitter Voltage	15	V
V _{EB0}	Emitter-Base Voltage	6.5	V
I _C	Collector Current -Continuous	500	mA
P _C	Collector Power Dissipation	200	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	15			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	6.5			V
Collector cut-off current	I _{CBO}	V _{CB} =20V, I _E =0			0.5	μA
Emitter cut-off current	I _{EBO}	V _{EB} =4V, I _C =0			0.5	μA
DC current gain	h _{FE}	V _{CE} =3V, I _C =100mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500mA, I _B =50mA			0.4	V
Transition frequency	f _T	V _{CE} =5V, I _C = 50mA, f=100MHz		150		MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		15		pF

CLASSIFICATION OF h_{FE}

Rank	Q	R	S
Range	120-270	180-390	270-560
MARKING	AAQ	AAR	AAS

